

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS ⁽¹⁾				
Forward-Current Transfer Ratio $I_C = 0.1\text{mA}$, $V_{CE} = 10\text{Vdc}$ $I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$ $I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$ $I_C = 50\text{mA}$, $V_{CE} = 10\text{Vdc}$ $I_C = 150\text{mA}$, $V_{CE} = 10\text{Vdc}$ $I_C = 0.1\text{mA}$, $V_{CE} = 10\text{Vdc}$ $I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$ $I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$ $I_C = 50\text{mA}$, $V_{CE} = 10\text{Vdc}$ $I_C = 150\text{mA}$, $V_{CE} = 10\text{Vdc}$	2N3634, 2N3636 2N3635, 2N3637	 55 90 100 100 60	 150 300	
Collector-Emitter Saturation Voltage $I_C = 10\text{mA}$, $I_B = 1.0\text{mA}$ $I_C = 50\text{mA}$, $I_B = 5.0\text{mA}$	$V_{CE(sat)}$		0.3 0.6	Vdc
Base-Emitter Saturation Voltage $I_C = 10\text{mA}$, $I_B = 1.0\text{mA}$ $I_C = 50\text{mA}$, $I_B = 5.0\text{mA}$	$V_{BE(sat)}$	0.65	0.8 0.9	Vdc

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Forward Current Transfer Ratio $I_C = 30\text{mA}$, $V_{CE} = 30\text{Vdc}$, $f = 100\text{MHz}$ 2N3634, 2N3636 2N3635, 2N3637	$ h_{fe} $	1.5 2.0	8.0 8.5	
Forward Current Transfer Ratio $I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$ 2N3634, 2N3636 2N3635, 2N3637	h_{fe}	40 80	160 320	
Small-Signal Short-Circuit Input Impedance $I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$ 2N3634, 2N3636 2N3635, 2N3637	h_{ie}	100 200	600 1200	Ω
Small-Signal Open-Circuit Input Impedance $I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$	h_{oe}		200	μs
Output Capacitance $V_{CB} = 20\text{Vdc}$, $I_E = 0$, $100\text{kHz} \leq f \leq 1.0\text{MHz}$	C_{obo}		10	pF
Input Capacitance $V_{EB} = 1.0\text{Vdc}$, $I_C = 0$, $100\text{kHz} \leq f \leq 1.0\text{MHz}$	C_{ibo}		75	pF
Noise Figure $V_{CE} = 10\text{Vdc}$, $I_C = 0.5\text{mA}$, $R_g = 1.0\text{k}\Omega$ $f = 100\text{Hz}$ $f = 1.0\text{kHz}$ $f = 10\text{kHz}$	NF		5.0 3.0 3.0	dB

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$



6 Lake Street, Lawrence, MA 01841
1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803
Website: <http://www.microsemi.com>

TECHNICAL DATA SHEET

Gort Road Business Park, Ennis, Co. Clare, Ireland
Tel: +353 (0) 65 6840044 Fax: +353 (0) 65 6822298

SAFE OPERATING AREA

DC Tests

$T_C = 25^{\circ}\text{C}$, 1 Cycle, $t = 1.0\text{s}$

Test 1

$V_{CE} = 100\text{Vdc}$, $I_C = 30\text{mA}$

2N3634, 2N3635

$V_{CE} = 130\text{Vdc}$, $I_C = 20\text{mA}$

2N3636, 2N3637

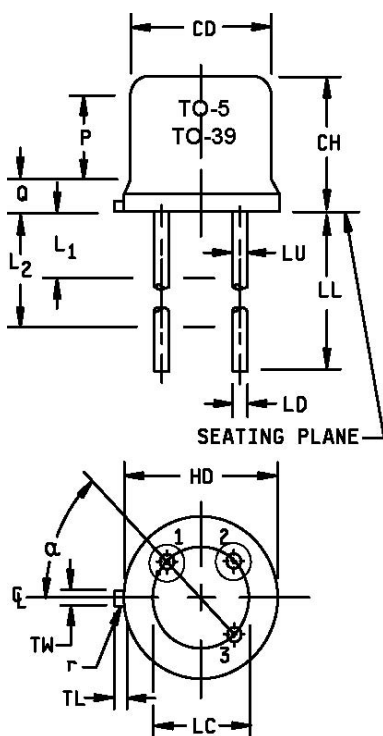
Test 2

$V_{CE} = 50\text{Vdc}$, $I_C = 95\text{mA}$

Test 3

$V_{CE} = 5.0\text{Vdc}$, $I_C = 1.0\text{A}$

PACKAGE DIMENSIONS

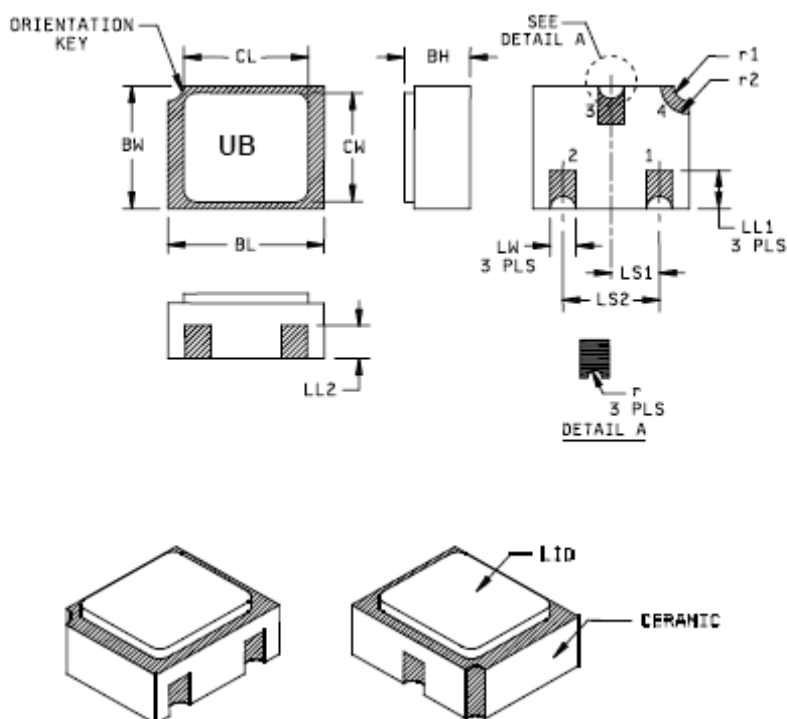


Ltr	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	
CH	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200 TYP		5.08 TYP		7
LD	.016	.021	0.41	0.53	6
LL	See notes 7, 9, and 10				
LU	.016	.019	0.41	0.48	7
L ₁		.050		1.27	7
L ₂	.250		6.35		7
P	.100		2.54		5
Q		.050		1.27	
r		.010		0.254	8
TL	.029	.045	0.74	1.14	4
TW	.028	.034	0.71	0.86	3
α	45° TP		45° TP		6
Term 1	Emitter				
Term 2	Base				
Term 3	Collector				

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Beyond r maximum, TW must be held to a minimum length of .021 inch (0.53 mm).
4. TL measured from maximum HD.
5. CD shall not vary more than ± 0.010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
6. Leads at gauge plane .054 - .055 inch (1.37 - 1.40 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at a maximum material condition (MMC) relative to the tab at MMC. The device may be measured by direct methods or by gauge and gauging procedure.
7. LU applies between L1 and L2. LD applies between L2 and L minimum. Diameter is uncontrolled in L1 and beyond LL minimum.
8. r (radius) applies to both inside corners of tab.
9. For transistor types 2N3634 through 2N3637, LL is .500 inch (12.70 mm) minimum, and .750 inch (19.05 mm) maximum (TO-39).
10. For transistor types 2N3634L through 2N3637L, LL is 1.500 inches (38.10 mm) minimum, and 1.750 inches (44.45 mm) maximum (TO-5).
11. In accordance with ASME Y14.5M, diameters are equivalent to ϕ x symbology.

FIGURE 1: Physical dimensions (TO-5 and TO-39)



NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Hatched areas on package denote metallized areas.
4. Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Shielding connected to the lid.
5. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology

Ltr	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
BH	.046	.056	1.17	1.42	
BL	.115	.128	2.92	3.25	
BW	.085	.108	2.16	2.74	
CL		.128		3.25	
CW		.108		2.74	
LL ₁	.022	.038	0.56	0.96	
LL ₂	.017	.035	0.43	0.89	
LS ₁	.036	.040	0.91	1.02	
LS ₂	.071	.079	1.81	2.01	
LW	.016	.024	0.41	0.61	
r		.008		.203	
r ₁		.012		.305	
r ₂		.022		.559	

FIGURE 2: Physical dimensions, surface mount 2N3634UB through 2N3637UB (UB version).